





PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

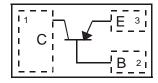
- **Epitaxial Die Construction**
- Complementary NPN Type Available (BC847BLP)
- Ultra-Small Leadless Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections Indicator: Collector Dot
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Ordering Information: See Page 3
- Marking Information: See Page 3
- Weight: 0.0009 grams







TOP VIEW (Internal Schematic)

DFN1006-3

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current	I _C	-100	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @T _A = 25°C	P_{D}	250	mW
Thermal Resistance, Junction to Ambient Air (Note 3) @T _A = 25°C	$R_{ heta JA}$	500	°C/W
Operating and Storage Temperature Range	T_i, T_{STG}	-55 to +150	°C

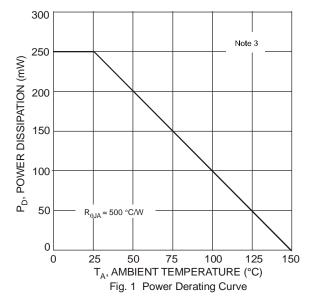
Electrical Characteristics @T_A = 25°C unless otherwise specified

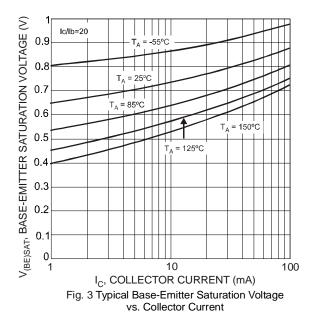
Characteristic (Note 4)	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-50	_	_	V	$I_C = 10 \mu A, I_B = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-45	_	_	V	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	_	_	V	$I_E = 1 \mu A, I_C = 0$
DC Current Gain	h _{FE}	220	260	475	_	$V_{CE} = -5.0V, I_{C} = -2.0mA$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		-90	-300	mV	$I_C = -10 \text{mA}, I_B = -0.5 \text{mA}$
Collector-Entitle Saturation Voltage	▼ CE(SAT)	V CE(SAT)	-250	-650		$I_C = -100 \text{mA}, I_B = -5.0 \text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	_	-700	_	mV	$I_C = -10 \text{mA}, I_B = -0.5 \text{mA}$
Dase Emilier Galdration Voltage	V BE(SAT)	_	-850	_		$I_C = -100 \text{mA}, I_B = -5.0 \text{mA}$
Base-Emitter Voltage	$V_{BE(ON)}$	-600	-670	-750	mV	$V_{CE} = -5.0V, I_{C} = -2.0mA$
Dase-Emiller Vollage	V BE(ON)		-710	-820	IIIV	$V_{CE} = -5.0V, I_{C} = -10mA$
Collector-Cutoff Current		I _{CBO} _	_	-15	nA	$V_{CB} = -30V$
Collector-Cuton Current	ICBO		_	-4.0	μΑ	$V_{CB} = -30V, T_A = 150$ °C
Gain Bandwidth Product	f	f _T 100	100 —	_	MHz	$V_{CE} = -5.0V, I_{C} = -10mA,$
Gain Danuwiutii Fibuuct	IŢ					f = 100MHz
Collector-Base Capacitance	Ссво		3.0	_	pF	$V_{CB} = -10V, f = 1.0MHz$

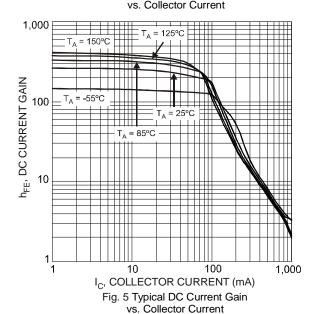
Notes:

- No purposefully added lead.
- Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php
- Device mounted on FR-4 PCB, pad layout as shown on page 3, or Diodes Inc. suggested pad layout document AP02001 on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- Short duration pulse test used to minimize self-heating effect.









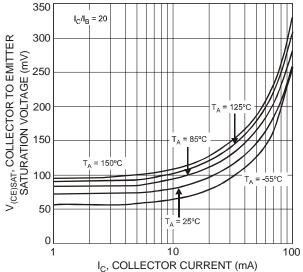


Fig. 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current

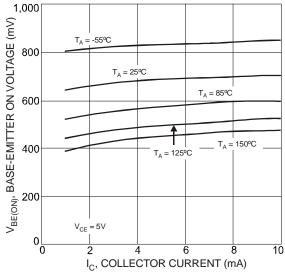


Fig. 4 Typical Base-Emitter Turn-On Voltage vs. Collector Current

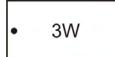


Ordering Information (Note 5)

Device	Packaging	Shipping
BC857BLP-7	DFN1006-3	3000/Tape & Reel

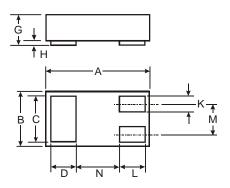
Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



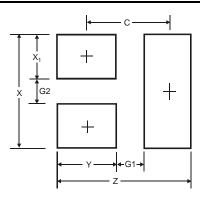
3W = Product Type Marking Code Dot Denotes Collector, Pin 3

Mechanical Details



DFN1006-3				
Dim	Min	Max	Тур	
Α	0.95	1.075	1.00	
В	0.55	0.675	0.60	
С	0.45	0.55	0.50	
D	0.20	0.30	0.25	
G	0.47	0.53	0.50	
Н	0	0.05	0.03	
K	0.10	0.20	0.15	
L	0.20	0.30	0.25	
M	_	_	0.35	
N	_	_	0.40	
All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
X	0.7
X1	0.25
Υ	0.4
С	0.7

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